

## 製品概要

### FFSPF1065A: SiC Diode - 650V, 10A, TO-220FP-2

技術情報は、データシートをご参照ください。

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost. Llew

## 特長

- Max Junction Temperature 175 °C
- High Surge Current Capacity
- Positive Temperature Coefficient
- No Reverse Recovery / No Forward Recovery

## アプリケーション

- PFC
- Industrial Power
- Solar
- EV Charger
- UPS

## 電気的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Device Grade	Configuration	V <sub>RRM</sub> (V)	I <sub>F(ave)</sub> (A)	V <sub>F</sub> (Max)	I <sub>FSM</sub> (A)	I <sub>R</sub> (Max) (μA)	Package Type
FFSPF1065A	2.1689	Pb-free	Active	Commercial	Single	650	10	1.75		200	TO-220FP / TO-220F-2FS

詳細は、弊社 [www.onsemi.jp](http://www.onsemi.jp) の営業または販売代理店にお問い合わせください。

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